

Electronic Supplementary Information

Engineering graphene and TMDs based van der Waals heterostructures for photovoltaic and photoelectrochemical solar energy conversion

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Table S1. Selected representative reports of graphene and TMDs based 2D/3D and 2D/2D heterostructure photoelectrodes in PEC cells.

Heterojunction type	Device structure	Photocurrent (mA/cm ²); applied bias	Onset potential (V vs. RHE)	Stability (J/J ₀); time; applied bias (V vs. RHE)	Electrolyte; light source	Ref .
Graphene/semiconductors	F-doped graphene/ <i>n</i> -Si photoanode	10; 0 V vs. E(A/A ⁻)	-0.27 V vs. E(A/A ⁻)	~100%; ~28 h; 0 V vs. E(A/A ⁻)	50 mM Fe(CN) ₆ ³⁻ and 350 mM Fe(CN) ₆ ⁴⁻ solution; W-halogen lamp illumination (~33 mW/cm ²)	320
	N-doped monolayer graphene/ <i>p</i> -Si NW photocathode	-27; 0 V vs. RHE	0.35	~30%; ~2.8 h; 0	1 M HClO ₄ solution (pH = 0); AM 1.5G (100 mW/cm ²)	321
	N-doped graphene quantum sheets/ <i>p</i> -Si NW photocathode	-35; 0 V vs. RHE	0.26	-	1 M HClO ₄ solution (pH = 0); AM 1.5G (100 mW/cm ²)	322
	FeNiCoO _x /graphene micro-net/ <i>n</i> -Si photoanode	19; 1.5 V vs. RHE	1.0	~71%; 1 h; 1.5	1 M NaOH solution (pH = 14); AM 1.5G (100 mW/cm ²)	325
	Graphene/Cu ₂ O photocathode	-4.8; 0 V vs. RHE	0.6	~83.3%; 20 min; 0	Na ₂ SO ₄ with 1.0 M buffer solution (pH = 5); AM 1.5G (100 mW/cm ²)	326
	BiV _{1-x} Mo _x O ₄ /graphene/α-Fe ₂ O ₃ photoanode	1.97; 1.6 V vs. RHE	0.27	~100%; 12 h; 1.2	0.01 M Na ₂ SO ₄ solution; AM 1.5G (100 mW/cm ²)	332
	NiFe-LDH/graphene/Ti O ₂ photoanode	1.74; 1.25 V vs. SCE	0.35	~100%; 5 h; 0.6 V vs. SCE	0.5 M Na ₂ SO ₄ solution (pH = 6.8); Xe lamp (100 mW/cm ²)	334
	MoS ₂ /N-graphene /g-C ₃ N ₄ photoanode	27.76 μA cm ⁻² at 0.8 V vs. Ag/AgCl	-	~100%; ~24 min; 0 V vs. Ag/AgCl	0.01 M Na ₂ SO ₄ solution (pH = 7); AM 1.5G (100 mW/cm ²)	336
TMDs/semiconductors	<i>p</i> -Cu ₂ O/graphene photocathode (CO ₂ reduction)	-0.75; 0.05 V vs. Ag/AgCl	-	~100%; 6 h; -0.05 and +0.05 V vs. Ag/AgCl	Phosphate buffer solution (pH = 4.0); AM 1.5G with a UV-cutoff filter	344
	FTO/f-RGO/rr-P3HT:PCBM/TiO ₂ /Pt photocathode	-6.01; 0 V vs. RHE	0.6	~57%; 20 h; 0	Sodium acetate/acetic acid buffer (pH = 4); AM 1.5G (100 mW/cm ²)	345
TMDs/semiconductors	Mo ₃ S ₄ / <i>p</i> -Si pillars photocathode	-8; 0 V vs. RHE	0.15	~100%; 1 h; 0	1 M HClO ₄ (pH = 0); AM 1.5G (>620 nm, 28.3 mW/cm ²)	347

MoS ₃ /p-InP pillars photocathode	-21; 0 V vs. RHE	0.6	~100%; 1 h; 0	1 M HClO ₄ ; AM 1.5G (100 mW/cm ²)	348
MoS _x /p-GaP photocathode	-6.4; 0 V vs. RHE	0.71	~100%; 5 h; 0	1 M HClO ₄ (pH = 0); AM 1.5G (100 mW/cm ²)	349
MoS ₂ /p-Si NW photocathode	-1; 0 V vs. RHE	0.25	~100%; 1 h; -0.1	Na ₂ SO ₄ with 1.0 M buffer solution (pH = 5); Xe lamp with a 420 nm cut-off filter (100 mW/cm ²)	350
MoS _x /Ti/n ⁺ p-Si photocathode	-16; 0 V vs. RHE	0.33	~100%; 1 h; 0.2	1 M HClO ₄ ; AM 1.5 G (>635 nm, 38.6 mW/cm ²)	351
MoS ₂ /TiO ₂ /Si photocathode	-15; 0 V vs. RHE	0.30	~100%; 1.25 h; -0.33	0.5 M H ₂ SO ₄ (pH = 0.48); AM 1.5G (100 mW/cm ²)	353
MoS ₂ /Al ₂ O ₃ /n ⁺ p Si photocathode	-32; 0 V vs. RHE	0.4	~100%; 120 h; 0	1 M HClO ₄ (pH = 0); AM 1.5G (100 mW/cm ²)	355
MoS _x /MoS ₂ /Mo/n ⁺ p-Si photocathode	-12; 0 V vs. RHE	0.334	~100%; 120 h; 0	1 M HClO ₄ ; AM 1.5 G (>635 nm, 39.5 mW/cm ²)	356
Mo ₃ S ₁₃ /MoS ₂ /Mo/Mo _x Si/n ⁺ p-Si photocathode	-17.5; 0 V vs. RHE	0.40	~100%; 100 h; 0	0.5 M H ₂ SO ₄ ; AM 1.5G (100 mW/cm ²)	357
MoS ₂ /MoO _x /SiO ₂ /MoSi _x /Si photocathode	-18.5; 0 V vs. RHE	0.31	~100%; 1538 h; 0	0.5 M H ₂ SO ₄ ; AM 1.5G (100 mW/cm ²)	358
MoS ₂ /Mo/GaInP ₂ photocathode	-6; 0 V vs. RHE	0.36	~100%; 70 h; -0.025	3 M H ₂ SO ₄ ; AM 1.5G (100 mW/cm ²)	359
MoS ₂ /p-Si photocathode	-21.4; 0 V vs. RHE	0.23	~100%; 24 h; -0.29	0.5 M H ₂ SO ₄ (pH = 0.3); AM 1.5G (100 mW/cm ²)	361
MoS ₂ (13 nm)/p-Si photocathode	-24.6; 0 V vs. RHE	0.17	~100%; 50 h; 0	0.5 M H ₂ SO ₄ (pH = 1.1); AM 1.5G (100 mW/cm ²)	362
WS ₂ (23 nm)/p-Si photocathode	-8.3; 0 V vs. RHE	0.2	~83%; 10 h; 0	0.5 M H ₂ SO ₄ (pH = 0.27); AM 1.5G (100 mW/cm ²)	364
1T-MoS ₂ /p-Si photocathode	-17.6; 0 V vs. RHE	0.25	~77%; 3 h; 0	0.5 M H ₂ SO ₄ ; AM 1.5G (100 mW/cm ²)	366
MoS _x Cl _y /p-Si photocathode	-20.6; 0 V vs. RHE	0.27	-	0.5 M H ₂ SO ₄ (pH = 0.16); AM 1.5G (100 mW/cm ²)	367
MoS _x Cl _y /p-Si micro-pyramids photocathode	-43.0; 0 V vs. RHE	0.41	~100%; 2 h; 0	0.5 M H ₂ SO ₄ ; AM 1.5G (100 mW/cm ²)	368

	MoSe _x Cl _y /p-Si micro-pyramids photocathode	-38.8; 0 V vs. RHE	0.35	~100%; 2 h; 0	0.5 M H ₂ SO ₄ ; AM 1.5G (100 mW/cm ²)	368
	a-CoMoS _x /Si photocathode	-17.5; 0 V vs. RHE	0.25	~93%; ~3.2 h; 0	Phosphate electrolyte (pH = 4.25); AM 1.5G (100 mW/cm ²)	370
	CoMoS _x /p-Si microwire photocathode	-17.2; 0 V vs. RHE	0.192	~67%; 8 h; 0	0.5 M H ₂ SO ₄ (pH = 0.3); AM 1.5G (100 mW/cm ²)	371
	MoO _x S _y /p-Si microwire photocathode	-9.83; 0 V vs. RHE	0.24	~100%; 2 h; 0	0.5 M K ₂ SO ₄ solution (pH = 1); AM 1.5G (IR filtered; 60 mW/cm ²)	372
	S:MoP/p-Si photocathode	-33.1; 0 V vs. RHE	0.28	~80%; 2.8 h; 0	0.5 M H ₂ SO ₄ (pH = 1.1); AM 1.5G (100 mW/cm ²)	373
	MoS _{2-x} /TiO ₂ /AZO/p-Cu ₂ O photocathode	-5.7; 0 V vs. RHE	0.45	~100%; 5 h at pH = 1, 10 h at pH = 4 or 9; 0	0.5 M Na ₂ SO ₄ with 0.2 M potassium hydrogen phthalate buffer; AM 1.5G (100 mW/cm ²)	316
Ultrathin TMDs photoelectrodes	WSe ₂ nanoflake photocathode (~25 nm)	-1.0; 0 V vs. RHE	0.5	~100%; 27 min; 0	1 M H ₂ SO ₄ solution (pH = 0); AM 1.5G (100 mW/cm ²)	423
	Edge-passivated WSe ₂ nanoflake photocathode (~18 nm)	-2.64; -0.37 V vs. Ag/AgCl	-0.2 V vs. Ag/AgCl	-	Chloranil in MeCN; AM 1.5G (100 mW/cm ²)	424
	Pre-annealed, HTS-passivated WSe ₂ nanoflake photocathode (~11 nm)	~-4; 0 V vs. RHE	0.4	~100%; > 2 h; 0	1 M H ₂ SO ₄ solution (pH = 0); AM 1.5G (100 mW/cm ²)	448
	MoS ₂ /perylene-diimide (PDI) photoanode (~10 nm)	~2.60; 0.1 V vs. Ag/AgCl	-0.3 V vs. Ag/AgCl	~100%; 300 s; 0.1 V vs. Ag/AgCl	25 mM LiI in 0.1 M TBAP acetonitrile solution; AM 1.5G (100 mW/cm ²)	426
	MoS ₂ /WS ₂ photoanode (~60 nm)	0.45; 1.23 V vs. RHE	0.6	~100%; 1 h; 1	0.5 M NaClO ₄ solution (pH = 1); AM 1.5G (100 mW/cm ²)	427
	ZnIn ₂ S ₄ /MoSe ₂ photoanode	-6.8; -0.8 V vs. SCE	-0.35 V vs. SCE	~87%; ~280 s; -	0.2 M Na ₂ SO ₄ (pH = 6.8 ; Xe lamp (λ >400 nm))	417
	Black phosphorus/WS ₂ photocathode	-2.25; -1 V vs. Ag/AgCl	-0.61 V vs. Ag/AgCl	~91%; ~240 s; 0.3 V vs. Ag/AgCl	0.1 M NaOH ethanol solution; Xe lamp (>780 nm irradiation)	461